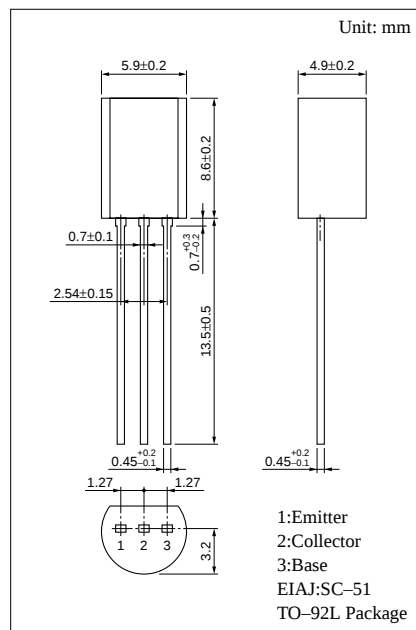


Silicon PNP epitaxial planer type

Complementary to 2SC1573

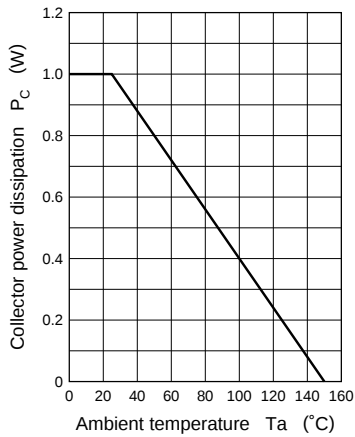
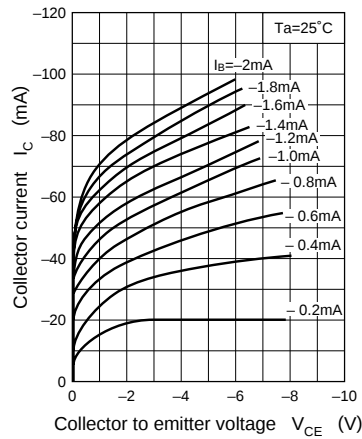
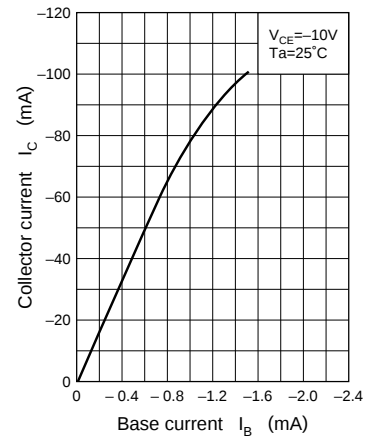
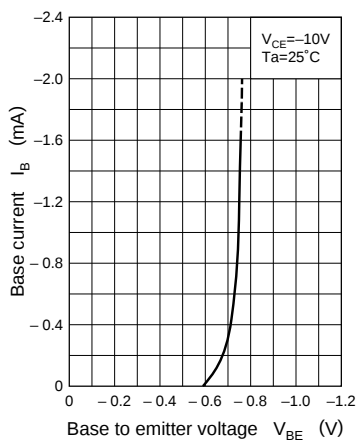
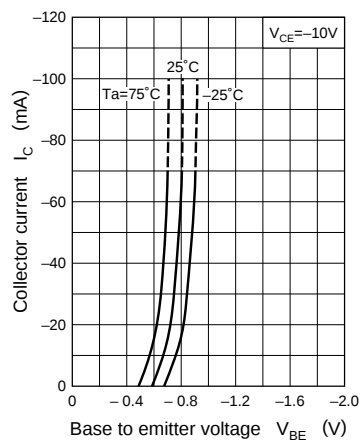
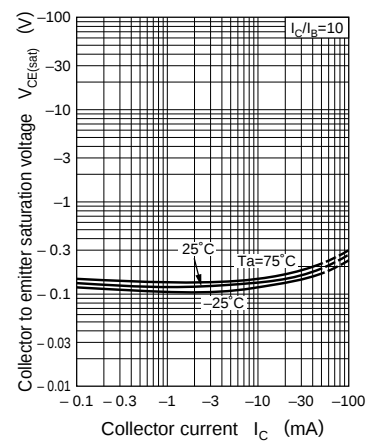
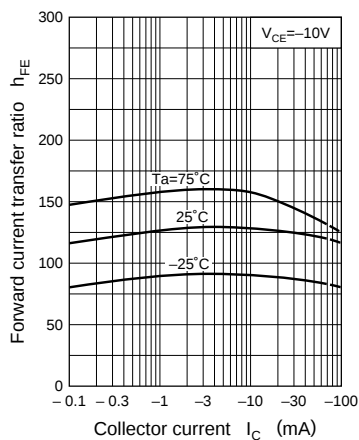
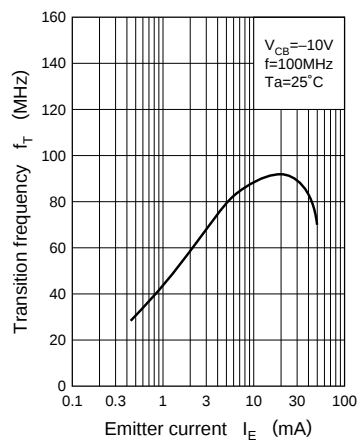
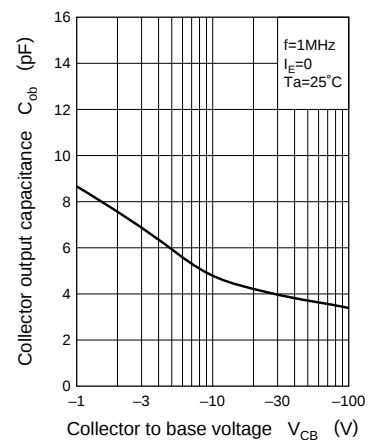
- High collector to emitter voltage V_{CE0} .

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	−250	V
Collector to emitter voltage	V_{CEO}	−200	V
Emitter to base voltage	V_{EBO}	−5	V
Peak collector current	I_{CP}	−100	mA
Collector current	I_C	−70	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 ~ +150	°C

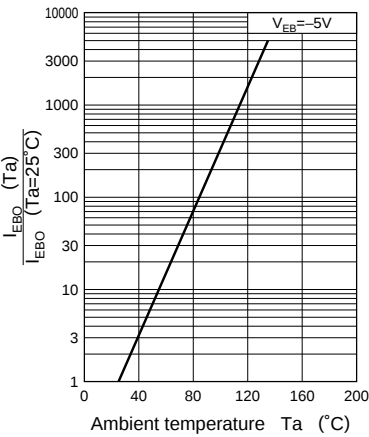


Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -12V, I_B = 0$			-2	μA
Collector to emitter voltage	V_{CEO}	$I_C = -100\mu A, I_B = 0$	-200			V
Emitter to base voltage	V_{EBO}	$I_E = -1\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = -10V, I_C = -5mA$	60		220	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1.5	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 10mA, f = 200MHz$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		5	10	pF

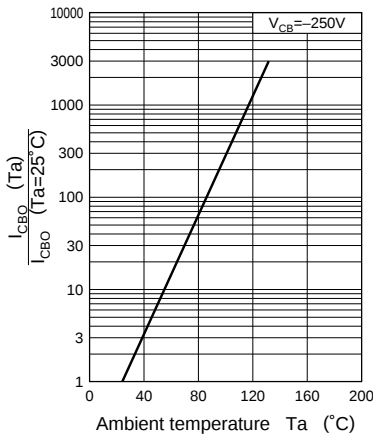
Rank	Q	R
h_{FE}	60 ~ 150	100 ~ 220

$P_C - T_a$  $I_C - V_{CE}$  $I_C - I_B$  $I_B - V_{BE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 

$I_{EBO} - T_a$



$I_{CBO} - T_a$



Area of safe operation (ASO)

